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June 2014

FQA36P15

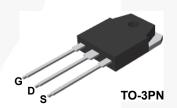
P-Channel QFET® MOSFET -150 V, -36 A, 90 mΩ

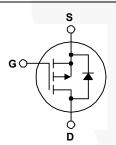
Features

- Low Gate Charge (Typ. 81 nC)
- Low Crss (Typ. 110 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating

Description

• -36 A, -150 V, $R_{DS(on)}$ = 90 m Ω (Max) @V_{GS} = -10 V, I_D = -18 A This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQA36P15	Unit
V_{DSS}	Drain-Source Voltage		-150	V
I _D	Drain Current - Continuous (T _C = 25°C)		-36	Α
	- Continuous (T _C = 100°C)		-25.5	А
I _{DM}	Drain Current - Pulsed	(Note 1)	-144	Α
V _{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		1400	mJ
I _{AR}	Avalanche Current (Note		-36	Α
E _{AR}	Repetitive Avalanche Energy (Note 1)		29.4	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		-5.0	V/ns
P_{D}	Power Dissipation (T _C = 25°C)		294	W
	- Derate above 25°C		1.96	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C	

Thermal Characteristics

Symbol	Parameter	FQA36P15	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.51	°C/W	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQA36P15	FQA36P15	TO-3PN	Tube	N/A	N/A	30 units

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter Test Conditions		Min	Тур	Max	Unit
Off Charac	teristics					
BV _{DSS}	Drain-Source Breakdown Voltage $V_{GS} = 0 \text{ V, I}_D = -250 \mu\text{A}$		-150			٧
$\Delta BV_{DSS}/$ ΔT_{J}	Breakdown Voltage Temperature Coefficient I_D = -250 μ A, Referenced to 25°C			-0.13		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -150 V, V _{GS} = 0 V			-10	μА
		$V_{DS} = -120 \text{ V}, T_{C} = 150^{\circ}\text{C}$			-100	μΑ
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = -25 V, V_{DS} = 0 V			-100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = 25 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
On Charact	eristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-2.0		-4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = -10 \text{ V}, I_D = -18 \text{ A}$		0.076	0.09	Ω
g _{FS}	Forward Transconductance	$V_{DS} = -40 \text{ V}, I_{D} = -18 \text{ A}$		19.5		S
Dynamic Cl	naracteristics					
C _{iss}	Input Capacitance	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$	\	2550	3320	pF
C _{oss}	Output Capacitance	f = 1.0 MHz	\	710	920	pF
C _{rss}	Reverse Transfer Capacitance			110	140	pF
Switching C	Characteristics					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = -75 \text{ V}, I_{D} = -36 \text{ A},$		50	110	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		350	710	ns
t _{d(off)}	Turn-Off Delay Time			155	320	ns
t _f	Turn-Off Fall Time	(Note 4)		150	310	ns
Qg	Total Gate Charge	$V_{DS} = -120 \text{ V}, I_{D} = -36 \text{ A},$	/	81	105	nC
Q _{gs}	Gate-Source Charge	V _{GS} = -10 V	/	19		nC
Q _{gd}	Gate-Drain Charge	(Note 4)	/ -	42		nC
Drain-Source	ce Diode Characteristics and Maximum Ratings					
Maximum Continuous Drain-Source Diode Forward Current					-36	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				-144	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = -36 A			-4.0	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = -36 A,		198		ns
Q _{rr}	Reverse Recovery Charge	$dI_F / dt = 100 A/\mu s$		1.45		μС

Notes

^{1.} Repetitive rating: pulse-width limited by maximum junction temperature.

^{2.} L = 1.45 mH, I_{AS} = -36 A, V_{DD} = -50 V, R_G = 25 Ω , starting T_J = 25°C.

^{3.} $I_{SD} \le$ -36 A, di/dt \le 300 A/ μ s, $V_{DD} \le$ BV $_{DSS}$, starting T $_J$ = 25°C.

^{4.} Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

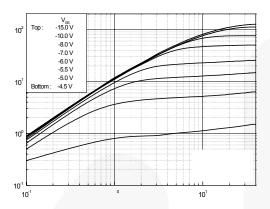


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

Figure 2. Transfer Characteristics

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

Figure 5. Capacitance Characteristics

Figure 6. Gate Charge Characteristics

Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature

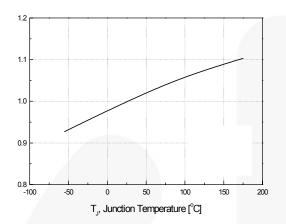


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

-V_{DS}, Drain-Source Voltage [V]

Figure 11. Transient Thermal Response Curve

 $Z_{\theta J\,C}(t)$, Thermal Response [°C/W]

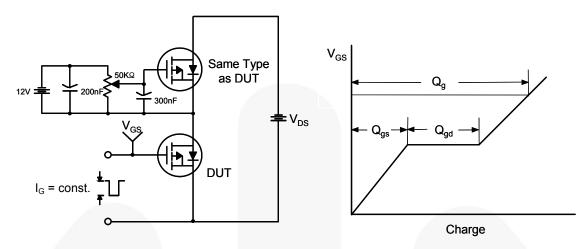


Figure 12. Gate Charge Test Circuit & Waveform

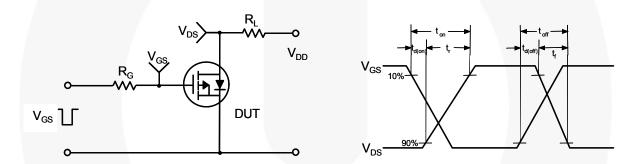


Figure 13. Resistive Switching Test Circuit & Waveforms

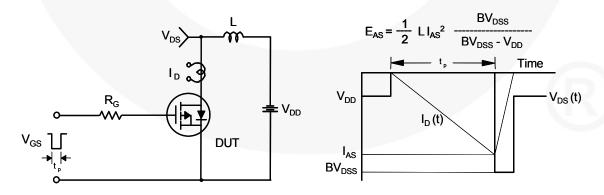


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

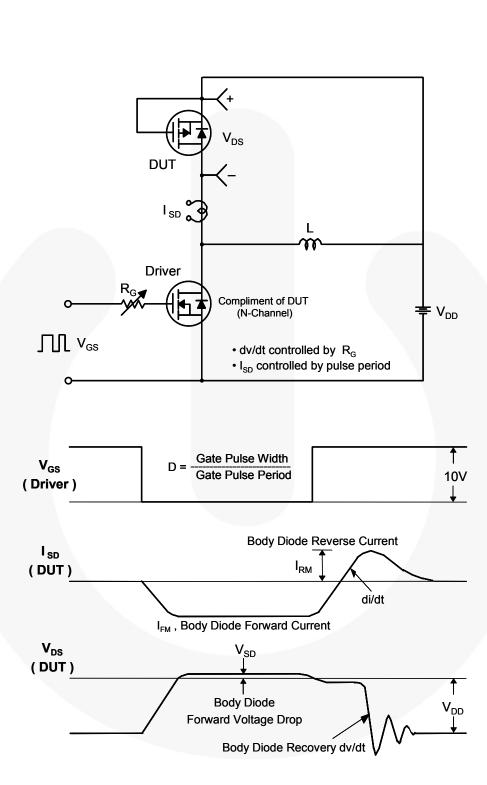


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

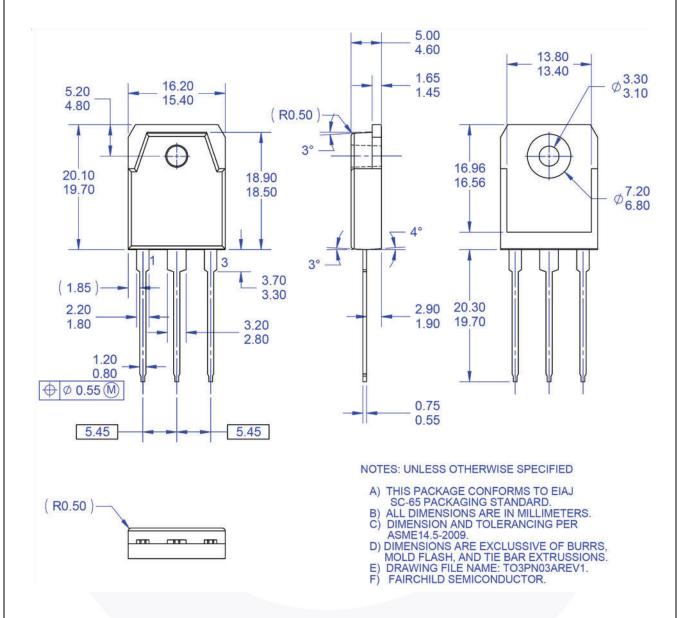


Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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